

AP8022H

800V

MOSFET

EMI

800V

MOSFET

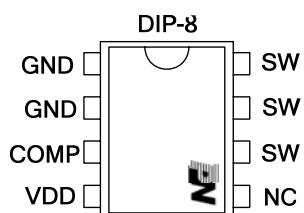
85~265V AC

10W

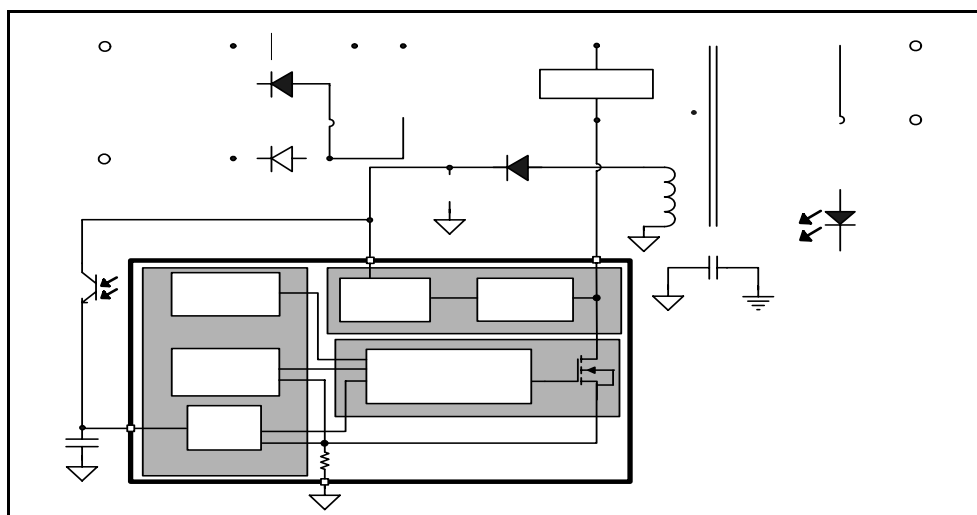
EMI

/

± OCP
 ± OTP
 ± VDD



AP8022HNEC-T1	DIP-8



1,2	GND	MOS
3	COMP	MOS
4	VDD	UVLO VDD
5	NC	
6,7,8	SW	

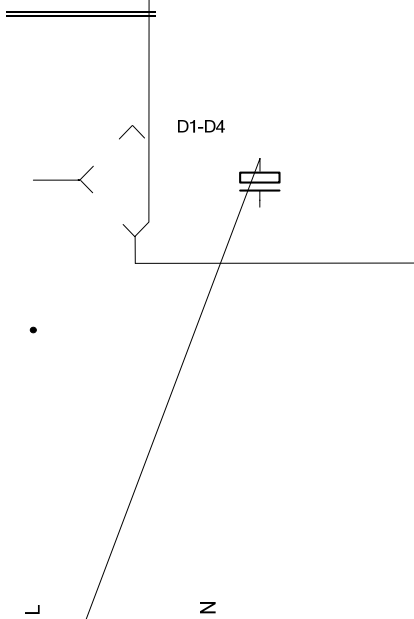
($T_J=25^\circ\text{C}$, $V_{DD}=15\text{ V}$)

3.

4.

V_{START}		$V_{COMP}=0\text{ V}$	13	14.5	16	V
V_{STOP}		$V_{COMP}=0\text{ V}$	7	8	9	V
V_{HYS}				6.5		V
V_{RST}	VDD		5.5	6	6.5	V
F_{OSC}		0 T_A 100°C	60	65	70	kHz
FD				±4		kHz
FM				88		Hz
D_{MAX}			70	80	90	%
I_{COMP}	COMP			1.2		mA
R_{COMP}	COMP			1.25		k
I_{LIM}		$T_A = 25^\circ\text{C}$	0.6	0.7	0.8	A
T_{LEB}		LEB time		350		ns
t_{SS}				10		ms
I_{D_BM}		$V_{COMP}=0.6\text{ V}$		150		mA

T_{SD}			140	170	-	°C
T_{HYST}				30		°C
I_{CH}	SW	$V_{DRAIN} = 120\text{ V},$ $V_{COMP} = \text{GND},$ $V_{DD} = 4\text{ V}$		-0.7		mA
I_{DD}				4		mA
V_{DD}		After turn-on	10		35	V
V_{OVP}	VDD		36	40	44	V
I_{DD_OFF}		$V_{DD} = 7\text{ V}$		300	500	uA



1.

AP8022H

SW

VDD

